

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

2SK4118LS— General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- · Adoption of high reliability HVP process.
- · Attachment workability is good by Mica-less package.
- · Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		400	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature	18	А
	I _{Dpack} *2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	11.9	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		427	mJ
Avalanche Current *5	IAV		18	А

^{*1} Shows chip capability

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Marking: K4118

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^{*2} Package limited

^{*3} SANYO's condition is radiation from backside.

^{*4} VDD=99V, L=2mH, IAV=18A

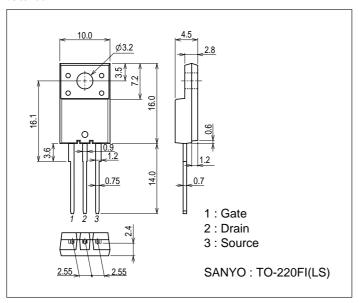
^{*5} L≤2mH, single pulse

Electrical Characteristics at Ta=25°C

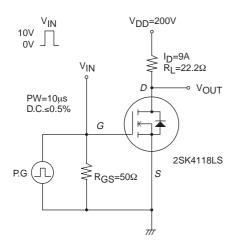
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	400			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =320V, V _{GS} =0V			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =9A	4	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =9A, V _{GS} =10V		0.26	0.34	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		1000		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		240		pF
Reverse Transfer Capacitance	Crss	V _{DS} =30V, f=1MHz		52		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		25		ns
Rise Time	t _r	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		108		ns
Fall Time	tf	See specified Test Circuit.		49		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =18A		38.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =18A		6.7		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =200V, V _{GS} =10V, I _D =18A		25		nC
Diode Forward Voltage	V _{SD}	IS=18A, VGS=0V		0.9	1.2	V

Package Dimensions

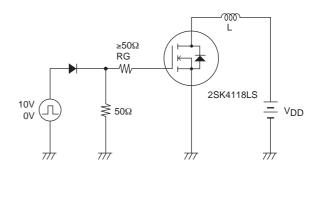
unit : mm (typ) 7509-002

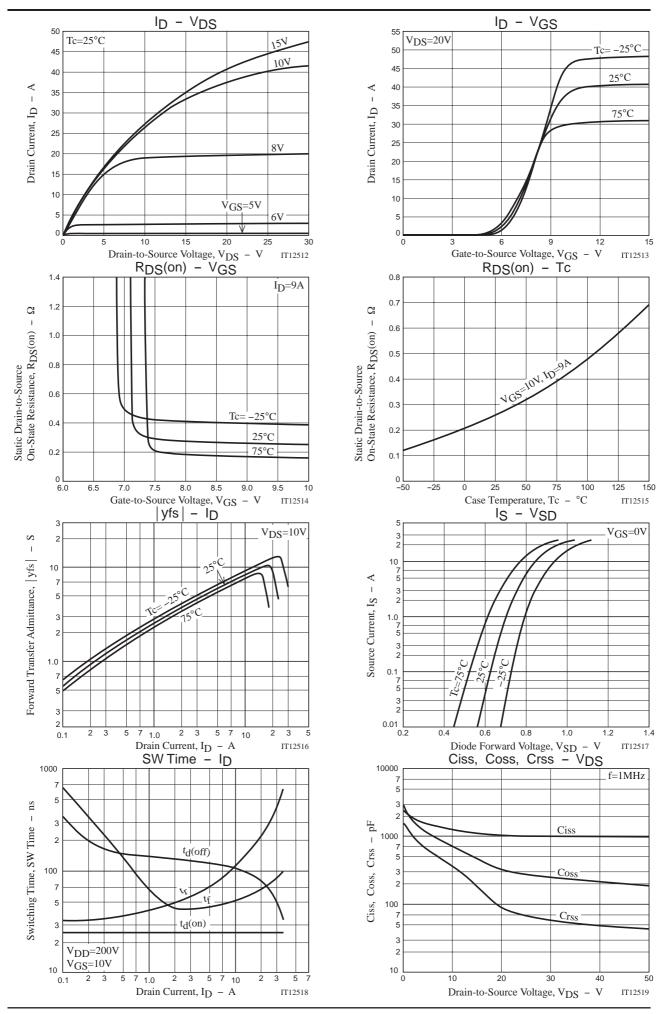


Switching Time Test Circuit

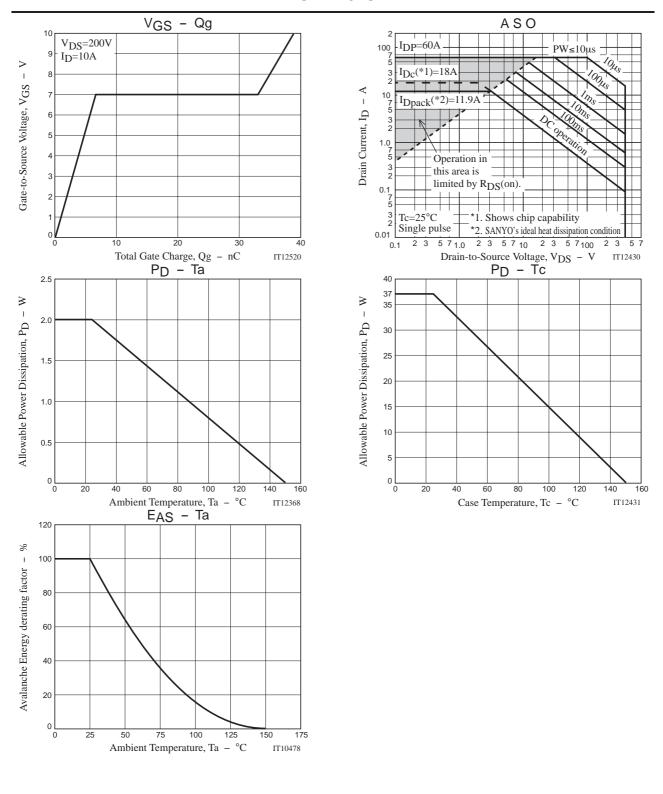


Avalanche Resistance Test Circuit





2SK4118LS



Note on usage : Since the 2SK4118LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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